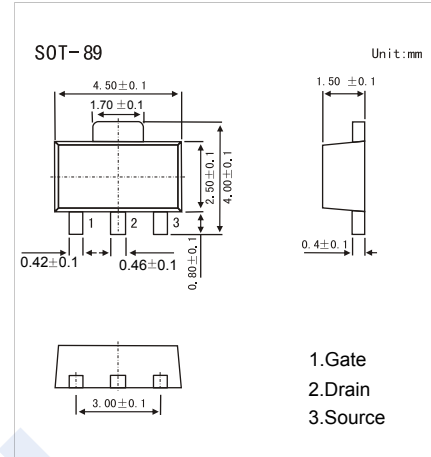
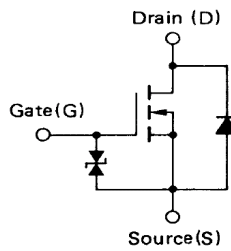


N-Channel MOSFET

2SK1584

■ Features

- $V_{DS} (V) = 30V$
- $I_D = 0.5 A$
- $R_{DS(ON)} < 1.5 \Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 2 \Omega (V_{GS} = 4V)$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	0.5	A
Pulsed Drain Current (Note.1)	I_{DM}	1	
Power Dissipation	P_D	2	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $PW \leq 10ms$, Duty Cycle $\leq 50\%$

■ Electrical Characteristics $T_a = 25^\circ C$

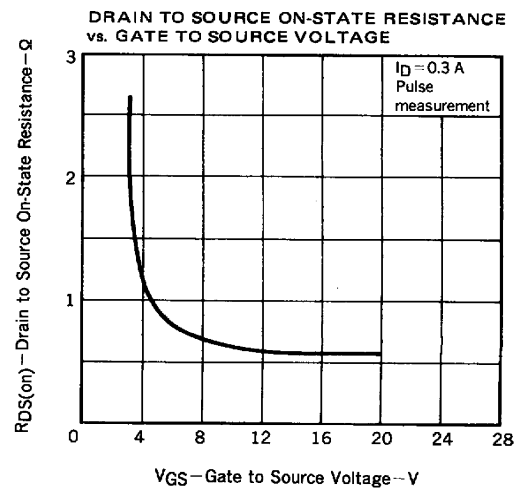
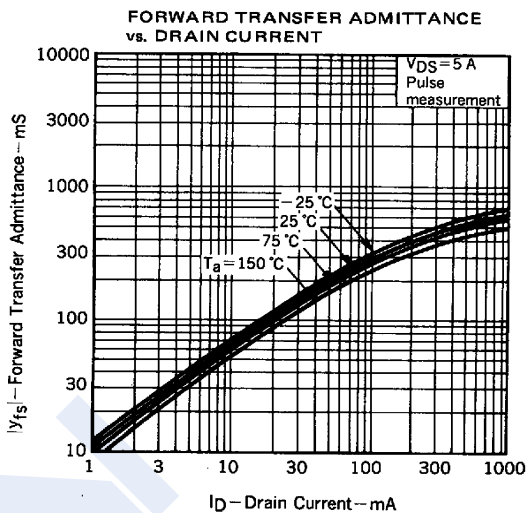
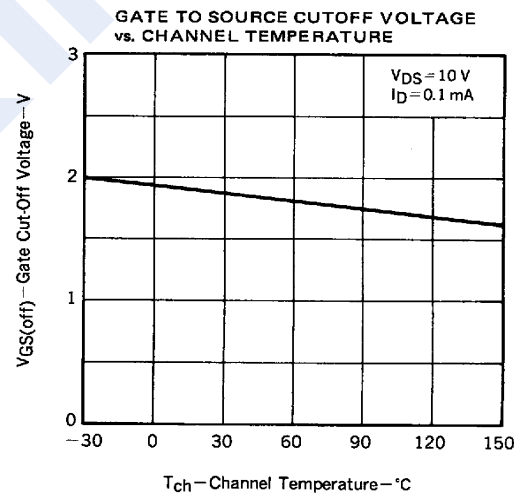
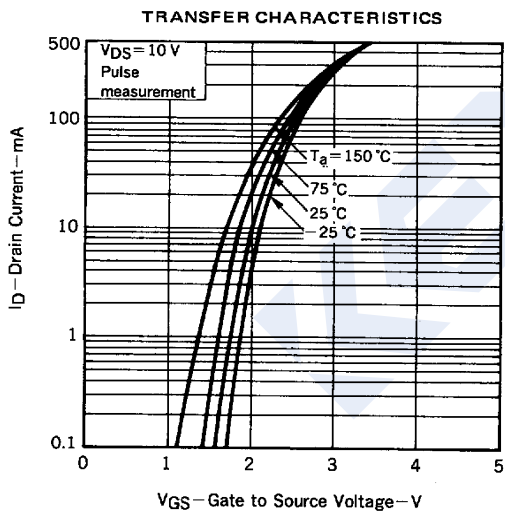
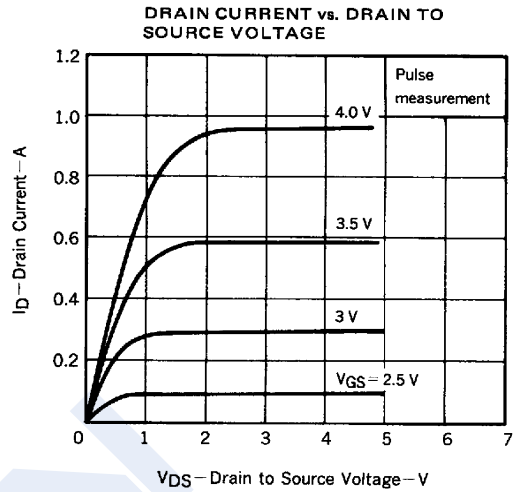
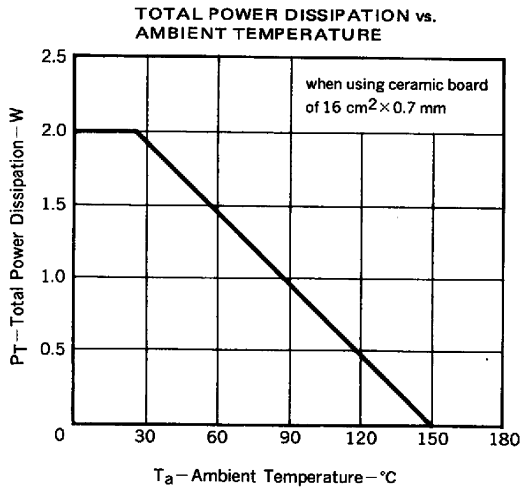
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = 250 \mu A, V_{GS} = 0V$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 10	μA
Gate Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = 10V, I_D = 0.1mA$	1.3		2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.3A$			1.5	Ω
		$V_{GS} = 4V, I_D = 0.3A$			2	
Forward Transconductance	g_{FS}	$V_{DS} = 5V, I_D = 0.5A$	350	440		mS
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 10V, f = 1MHz$		60		pF
Output Capacitance	C_{oss}			50		
Reverse Transfer Capacitance	C_{rss}			9		
Turn-On Delay Time	$t_{d(on)}$				80	
Turn-On Rise Time	t_r	$V_{GS(on)} = 4V, V_{DS} = 10V, I_D = 0.3A, R_L = 33 \Omega, R_G = 10 \Omega$		270		
Turn-Off Delay Time	$t_{d(off)}$			100		
Turn-Off Fall Time	t_f			110		

■ Marking

Marking	NH
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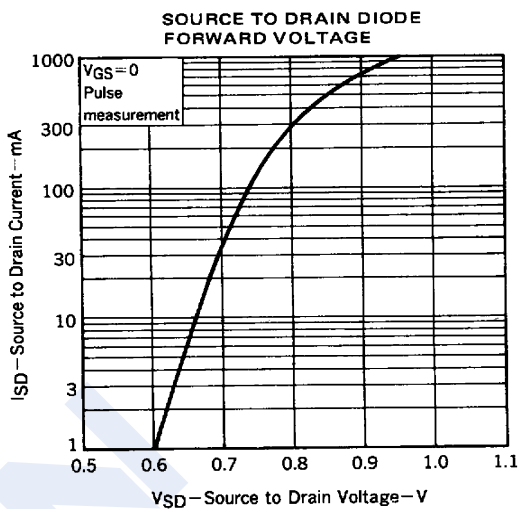
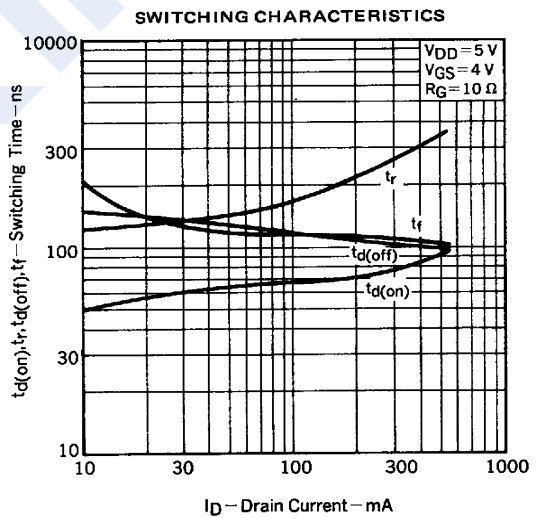
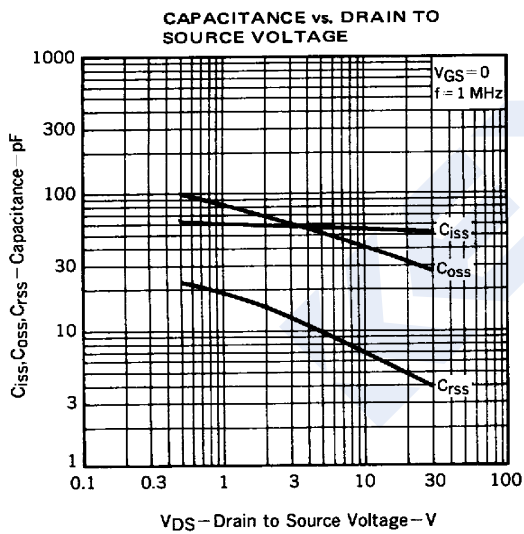
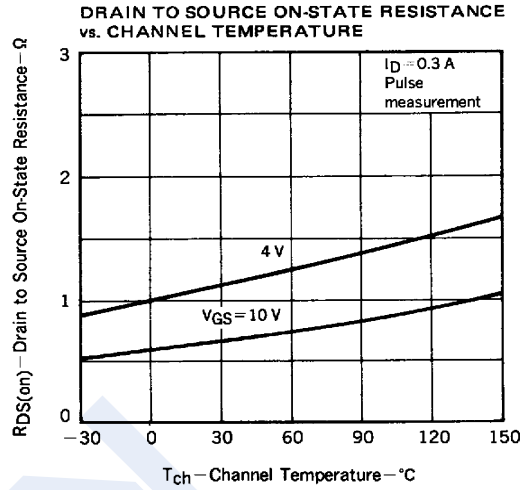
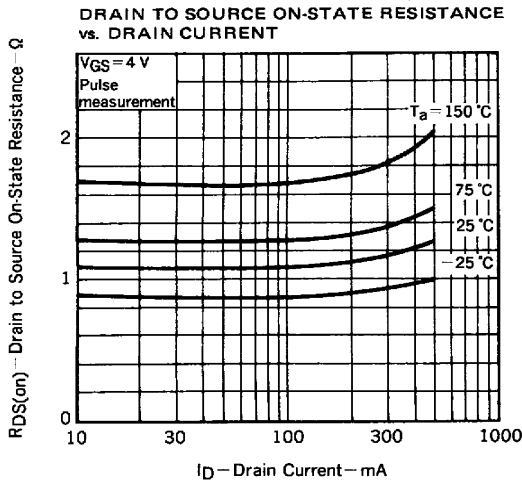
N-Channel MOSFET 2SK1584

■ Typical Characteristics



N-Channel MOSFET 2SK1584

Typical Characteristics



N-Channel MOSFET 2SK1584

■ Typical Characteristics

